

IN THE CLAIMS

Please amend the following claims which are pending in the present application:

1. (Currently amended) A method for drying circuit substrates (13), in particular semiconductor substrates, in which a circuit surface (29, 30) of the circuit substrate is flushed using a flushing liquid (10) in a flushing step and the circuit surface is dried in a subsequent drying step, the circuit substrate being moved in the flushing step in the direction of its planar extension transversely and in relation to a liquid level (28) of the flushing liquid in such a way that a liquid meniscus (31, 32) forms at a transition area (35) between the circuit surface and the liquid level, which changes because of the relative movement, and thermal radiation (36) is applied to the transition area wetted by the liquid meniscus in the drying step.
2. (Original) The method according to Claim 1,
characterized in that
thermal radiation (36) is applied using an infrared radiator.
3. (Currently amended) The method according to Claim 1 or 2,
characterized in that

to perform the relative movement between the liquid level (28) and the circuit substrate (13), the circuit substrate is situated in the flushing liquid (10) received by bath container (11) and the liquid level is lowered.

4. (Currently amended) The method according to ~~one of the preceding claims~~

Claim 1,

characterized in that

thermal radiation (36) is applied transversely to the liquid level (28).

5. (Currently amended) The method according to ~~one of the preceding claims~~

Claim 1,

characterized in that

the ventilation of a container lumen (33) implemented above the liquid level (28) occurs essentially parallel to the liquid level (28).

6. (Currently amended) The method according to ~~one of the preceding claims~~

Claim 1,

characterized in that

multiple flushing steps are performed through repeated flooding of the bath container before performing the drying step in the bath container (11).

7. (Currently amended) A device for performing a method for drying circuit substrates (13), in particular semiconductor substrates, according to ~~one more of~~ Claim[[s]] 1 ~~through~~ 6, having a bath container (11), which is provided with an inflow unit (16) and an outflow unit (17) and is closable using a cover unit (20), and a receiving system (12), which is situated in the bath container, for receiving at least one circuit substrate in such a way that the circuit substrate extends in a plane in the direction of a container floor (14), and having a thermal radiator unit (22) situated above the receiving system.

8. (Original) The device according to Claim 7,
characterized in that
the thermal radiator unit (22) is provided with infrared radiators.

9. (Currently amended) The device according to Claim 7 ~~or~~ 8,
characterized in that
the thermal radiator unit (22) is situated on the cover unit (20).

10. (Currently amended) The device according to ~~one or more~~ Claim[[s]] 7
~~through~~ 9,
characterized in that
the thermal radiator unit (22) is situated above a transparent plate (25) for separation from a container interior.

11. (Currently amended) The device according to ~~one of~~ Claim[[s]] 7 through 10,

characterized in that

the bath container (11) is provided in the area of the cover unit (20) with a ventilation unit (27).

12. (Original) The device according to Claim 11,

characterized in that

the ventilation unit (27) is situated on the cover unit (20).